

Vishay Siliconix

Do

Dual N-Channel 30-V (D-S) MOSFET

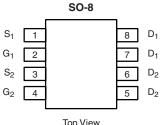
PRODUCT SUMMARY					
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)			
30	0.036 at V _{GS} = 10 V	5.9			
	0.053 at V _{GS} = 4.5 V	4.9			

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- Compliant to RoHS Directive 2002/95/EC

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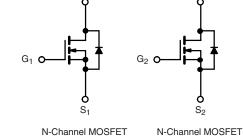




Top View

Ordering Information: Si4936ADY-T1-E3 (Lead (Pb)-free)

Operating Junction and Storage Temperature Range



- 55 to 150

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted Parameter Symbol 10 s **Steady State** Unit **Drain-Source Voltage** V_{DS} 30 ٧ Gate-Source Voltage V_{GS} ± 20 $T_A = 25 \degree C$ 5.9 4.4 Continuous Drain Current (T_J = 150 °C)^a I_D T_A = 70 °C 4.7 3.6 А **Pulsed Drain Current** I_{DM} ± 30 1.7 0.9 Continuous Source Current (Diode Conduction)^a I_S T_A = 25 °C 2.0 1.1 P_D Maximum Power Dissipation^a W $T_A = 70 \degree C$ 1.3 0.7

Si4936ADY-T1-GE3 (Lead (Pb)-free and Halogen-free)

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Manimum lumation to Amhianta	t ≤ 10 s	R _{thJA}	50	62.5		
Maximum Junction-to-Ambient ^a	Steady State		90	110	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	32	40		

T_J, T_{stg}

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

°C

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static				·			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$ 1.0			3.0	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
7	I _{DSS}	$V_{DS} = 30 V, V_{GS} = 0 V$			1	μA	
Zero Gate Voltage Drain Current		V_{DS} = 30 V, V_{GS} = 0 V, T_{J} = 55 °C			5		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5$ V, V_{GS} = 10 V	30			А	
	Б	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 5.9 \text{ A}$		0.032	0.036		
Drain-Source On-State Resistance ^a	$R_{DS(on)}$ $V_{GS} = 4.1$	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 4.9 \text{ A}$		0.042	0.053	Ω	
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 5.9 \text{ A}$		15		S	
Diode Forward Voltage ^a	V_{SD}	$I_{S} = 1.7 \text{ A}, V_{GS} = 0 \text{ V}$		0.8	1.2	V	
Dynamic ^b			•				
Total Gate Charge	Qg			13	20		
Gate-Source Charge	Q _{gs}	V_{DS} = 15 V, V_{GS} = 10 V, I_{D} = 5.9 A		2.3		nC	
Gate-Drain Charge	Q _{gd}			2.0		1	
Turn-On Delay Time	t _{d(on)}			6	12		
Rise Time	t _r	V_{DD} = 15 V, R_L = 15 Ω		14	25	1	
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong$ 1 A, V_GEN = 10 V, R_G = 6 Ω		30	60	ns	
Fall Time	t _f			5	10		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 1.7 A, dl/dt = 100 A/μs		30	60		

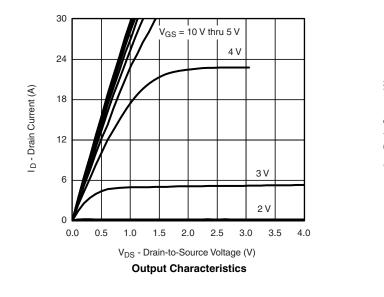
Notes:

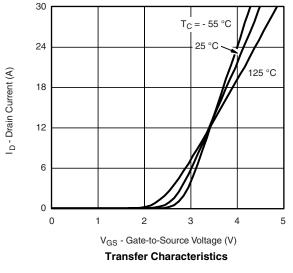
a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

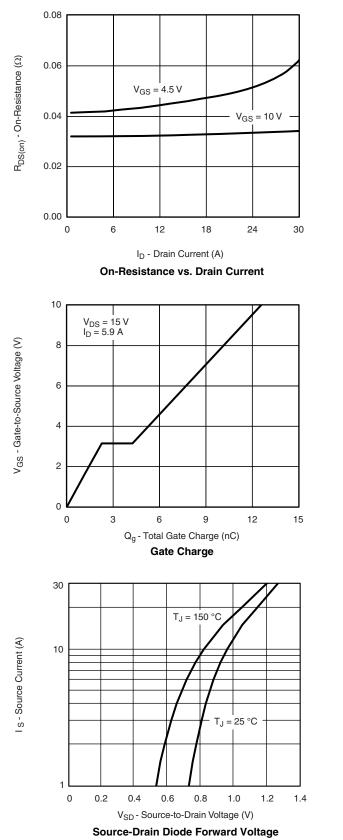


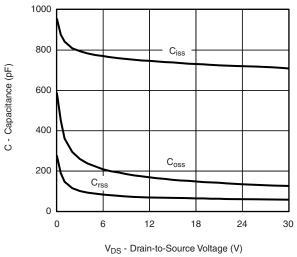




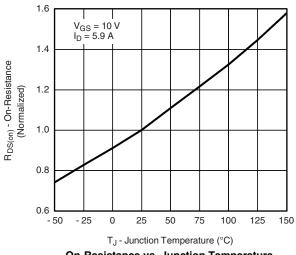
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

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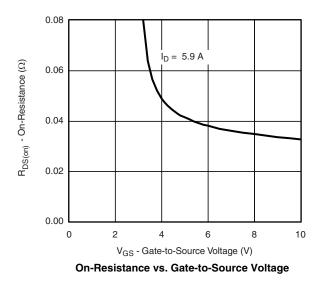




Capacitance



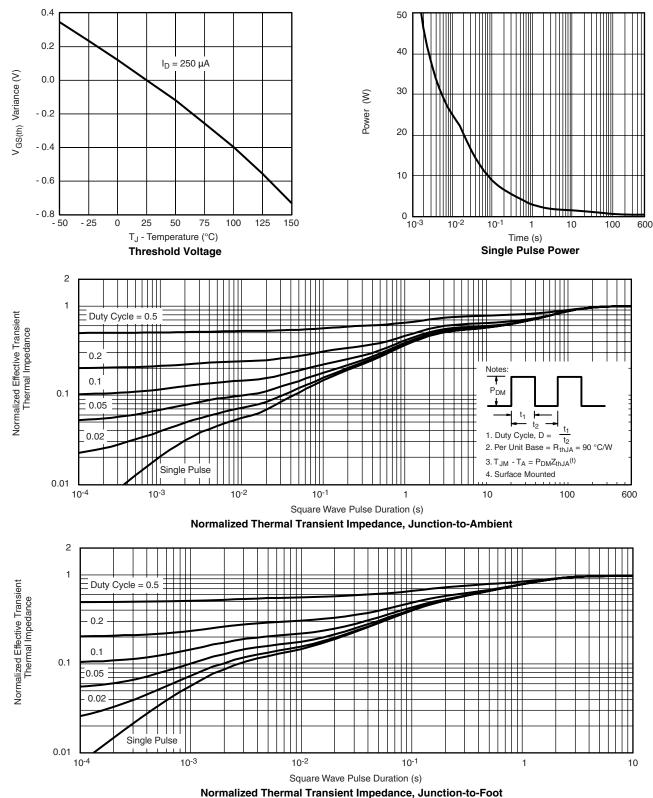
On-Resistance vs. Junction Temperature



Si4936ADY

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?71132.

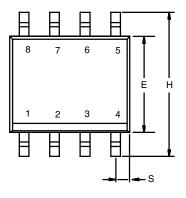
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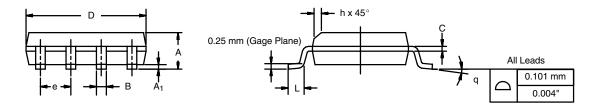


Package Information

Vishay Siliconix

SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012





	MILLIM	IETERS	INCHES			
DIM	Min	Мах	Min	Max		
A	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
E	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498						

Application Note 826

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RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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